

N-channel TrenchMOS standard level FET 28 July 2016

Product data sheet

1. General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12V, 24V and 48V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qu	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	80	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	349	W
Static charac	teristics	I					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11		-	3.1	3.8	mΩ
Dynamic characteristics							
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 64 V; Fig. 13; Fig. 14		-	51	-	nC

[1] Continuous current is limited by package.

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UFA
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK763R8-80E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK763R8-80E	BUK763R8-80E

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	80	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	80	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	349	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	120	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	120	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3		-	778	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
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Symbol	Parameter	Conditions		Min	Мах	Unit
Source-drain diode						
I _S	source current	T _{mb} = 25 °C	[1]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	778	А
Avalanche rug	Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ I_D = 120 \text{ A}; V_{sup} \le 80 \text{ V}; \text{ R}_{GS} = 50 \Omega; V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ unclamped}; Fig. 4 $	[2][3]	-	488	mJ

[1]

Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [2]

[3] Refer to application note AN10273 for further information.

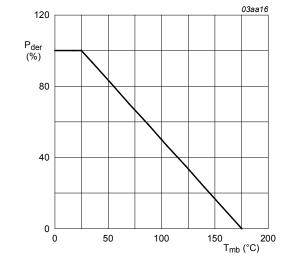
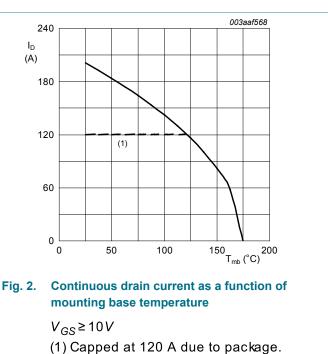


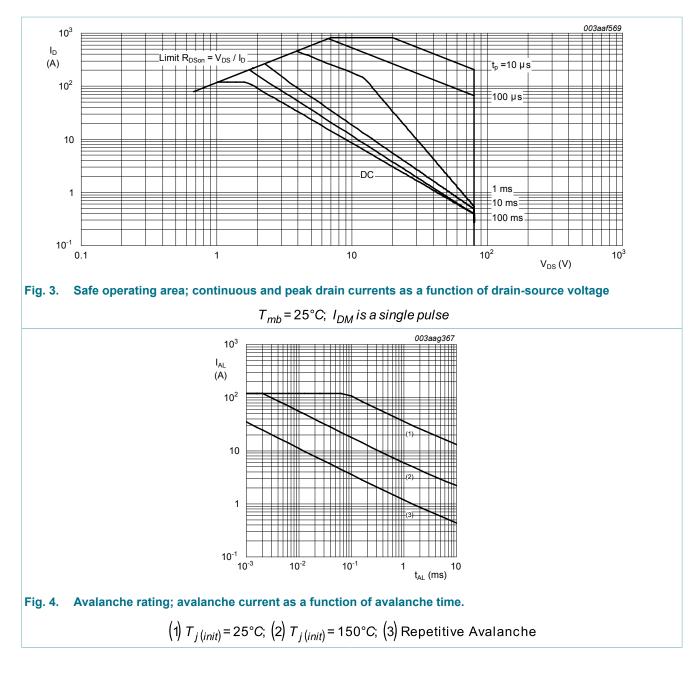
Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



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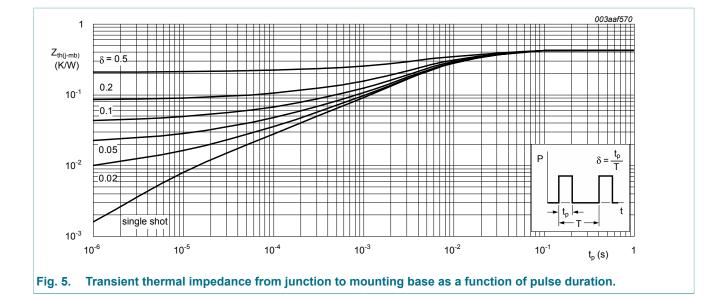
9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.43	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

Table 6. Thermal characteristics

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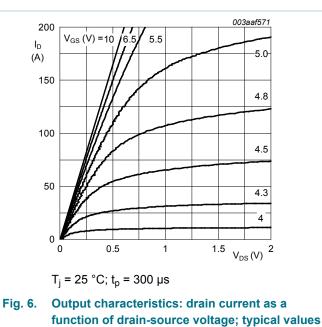


10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		I			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	80	-	-	V
	breakdown voltage	I_D = 250 mA; V_{GS} = 0 V; T_j = -55 °C	72	-	-	V
V _{GS(th)} gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V	
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1	-	-	V	
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V	
drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.15	1	μA	
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS} gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	3.1	3.8	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	9.2	mΩ
Dynamic ch	naracteristics		i			
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 10 \text{ V};$	-	169	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	37	-	nC
Q _{GD}	gate-drain charge		-	51	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;		-	9020	12030	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	840	1010	pF
C _{rss}	reverse transfer capacitance			-	470	645	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R _L = 2.4 Ω; V _{GS} = 10 V;		-	38	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$		-	48	-	ns
t _{d(off)}	turn-off delay time			-	129	-	ns
t _f	fall time			-	65	-	ns
L _D	internal drain inductance	from upper edge of mounting base to centre of die		-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad; $T_j = 25 \ ^{\circ}C$		-	7.5	-	nH
Source-dra	in diode		<u> </u>				
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>		-	0.77	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V _{GS} = 0 V;		-	58	-	ns
Qr	recovered charge	V _{DS} = 25 V		-	121	-	nC



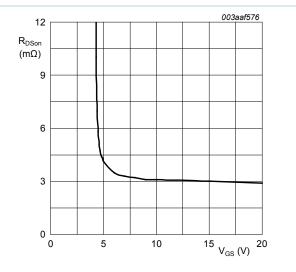
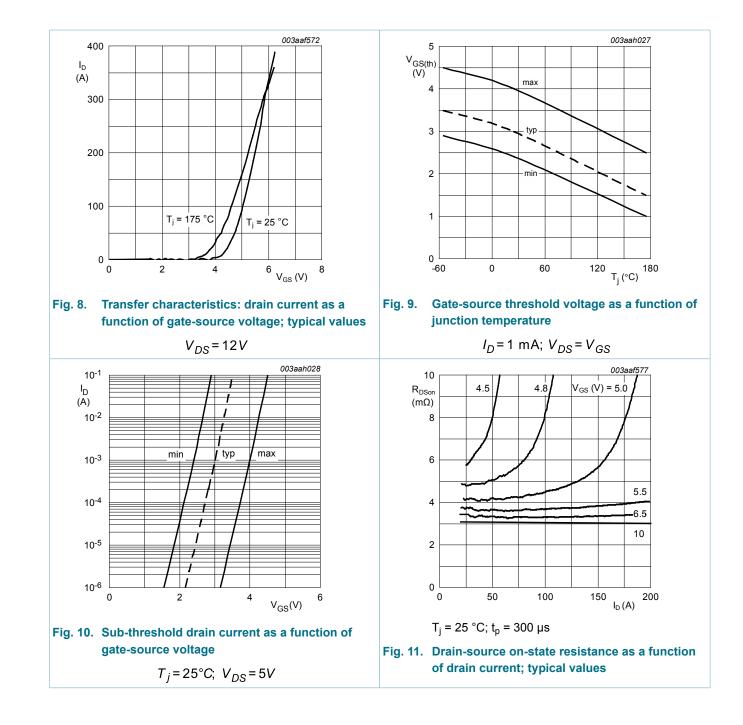


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25 \,^{\circ}C; I_D = 25A$

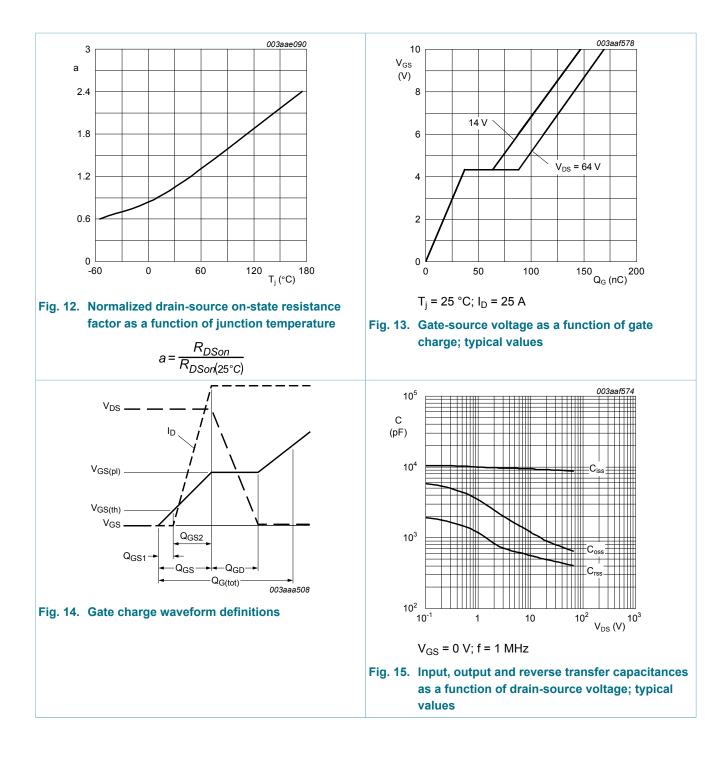
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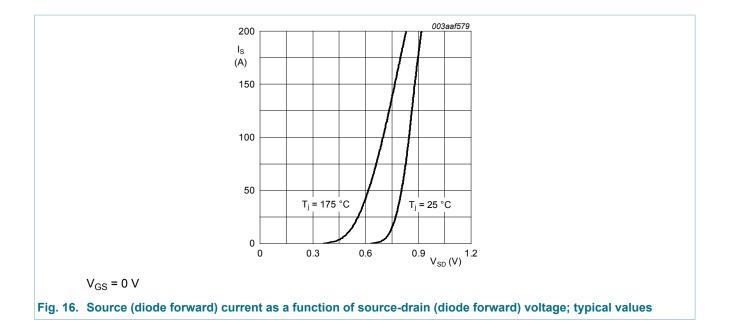
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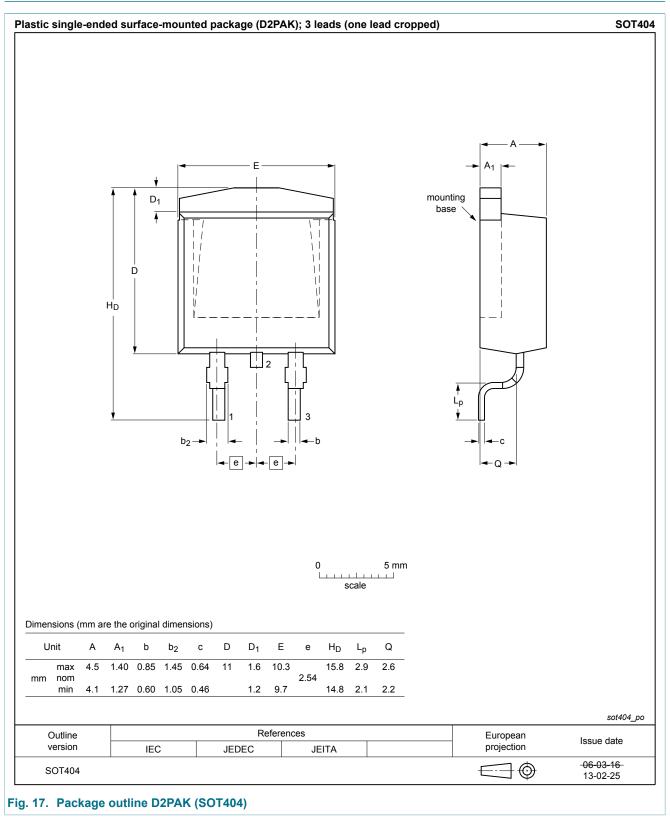
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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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